



Patent
Attorney's Docket No. 015290-504

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)	
Tuqiang NI et al.)	
Application No.: 09/883,207)	Group Art Unit: 1765
Filed: June 19, 2001)	Examiner: D.V. Deo
For: PLASMA ETCHING OF SILICON)	Confirmation No.: 9862
CARBIDE)	
)	

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AMENDMENT/REPLY TRANSMITTAL LETTER

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Enclosed is a reply for the above-identified patent application.

- ☐ A Petition for Extension of Time is also enclosed.
- ☐ A Terminal Disclaimer and the ☐ \$55.00 (2814) ☐ \$110.00 (1814) fee due under 37 C.F.R. § 1.20(d) are also enclosed.
- ☐ Also enclosed is/are _____.
- ☐ Small entity status is hereby claimed.
- ☐ Applicant(s) request continued examination under 37 C.F.R. § 1.114 and enclose the ☐ \$375.00 (2801) ☐ \$750.00 (1801) fee due under 37 C.F.R. § 1.17(e).
- ☐ Applicant(s) previously submitted __, on __, for which continued examination is requested.
- ☐ Applicant(s) request suspension of action by the Office until at least __, which does not exceed three months from the filing of this RCE, in accordance with 37 C.F.R. § 1.103(c). The required fee under 37 C.F.R. § 1.17(i) is enclosed.
- ☐ A Request for Entry and Consideration of Submission under 37 C.F.R. § 1.129(a) (1809/2809) is also enclosed.
- ☒ No additional claim fee is required.

☐ An additional claim fee is required, and is calculated as shown below:

AMENDED CLAIMS					
	NO. OF CLAIMS	HIGHEST NO. OF CLAIMS PREVIOUSLY PAID FOR	EXTRA CLAIMS	RATE	ADDT'L FEE
Total Claims		MINUS =		× \$18.00 (1202) =	
Independent Claims		MINUS =		× \$84.00 (1201) =	
If Amendment adds multiple dependent claims, add \$280.00 (1203)					
Total Amendment Fee					
If small entity status is claimed, subtract 50% of Total Amendment Fee					
TOTAL ADDITIONAL FEE DUE FOR THIS AMENDMENT					-0-

☐ A claim fee in the amount of \$_____ is enclosed.

☐ Charge \$_____ to Deposit Account No. 02-4800.

The Commissioner is hereby authorized to charge any appropriate fees under 37 C.F.R. §§ 1.16, 1.17, 1.20(d) and 1.21 that may be required by this paper, and to credit any overpayment, to Deposit Account No. 02-4800. This paper is submitted in duplicate.

Respectfully submitted,

BURNS, DOANE, SWECKER & MATHIS, L.L.P.

By: _____

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Date: April 8, 2003

#7/A
4/10/03
Patent

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AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Official Action dated January 14, 2003, please amend the present application as follows.

IN THE SPECIFICATION:

A marked-up version of the specification showing insertions and deletions appears in Appendix A. On pages 16-17, please rewrite paragraph 36 as follows:

A₁
Figure 1 illustrates the bowed etch profile obtained when using an etch gas mixture which includes O₂ but not SO₂ and Figure 2 illustrates the tapered etch profile obtained when the etch gas mixture includes SO₂ but not O₂. In Figure 1, a dielectric layer 2 having bowed openings 4 was obtained when the dielectric etch was carried out for about 4 minutes in a single step with the chamber pressure set at about 50 mTorr, one or both of the electrodes powered with 500 watts at 27 MHz and 2000 watts at 2 MHz, 500 sccm Ar, 7